

SCT019H120G3AG-VB Datasheet

N-Channel 1200V (D-S) SiC Power MOSFET

PRODUCT SUMMARY

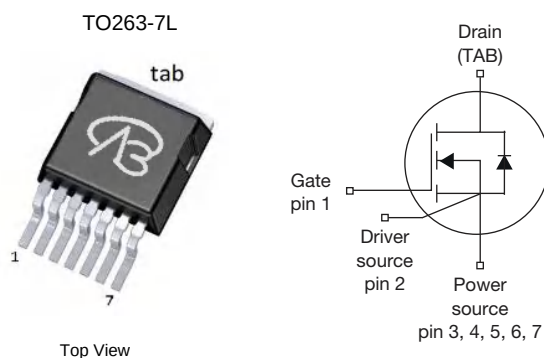
V_{DS} (V)	1200	
$R_{DS(on)}$ at 25 °C (Ω)	$V_{GS} = 18$ V	0.015
Q_g (nC)	200	

FEATURES

- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Higher robustness and system reliability
- Kelvin source provides up to 4 times lower switching losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)

APPLICATIONS

- Server and telecom power supplies
- EV charging infrastructure
- Solar PV inverters
- DC/DC converter



ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	1200	V
Gate-Source Voltage			V _{GS}	-10 / +22	
Continuous Drain Current (T _J = 175 °C)	V _{GS} at 18 V	T _C = 25 °C	I _D	142	A
		T _C = 100 °C		100	
Pulsed Drain Current ^a			I _{DM}	310	
Linear Derating Factor				2.1	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	625	mJ
Maximum Power Dissipation			P _D	535	W
Operating Junction and Storage Temperature Range			T _J , T _{stg}	-55 to +175	°C
Drain-Source Voltage Slope	T _J = 125 °C		dV/dt	150	V/ns
Reverse Diode dV/dt ^d				100	
Soldering Recommendations (Peak Temperature) ^c	for 10 s			260	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 0.5$ mH, $R_g = 25$ Ω .
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C.

THERMAL RESISTANCE RATINGS

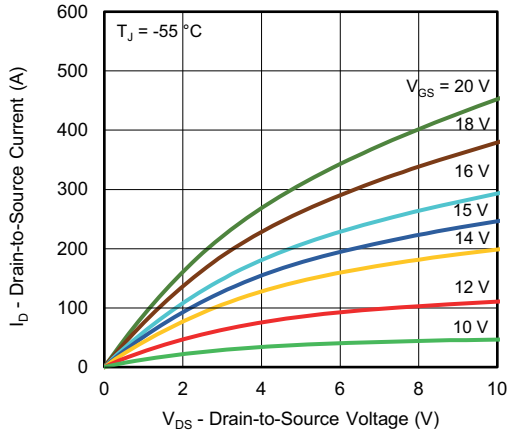
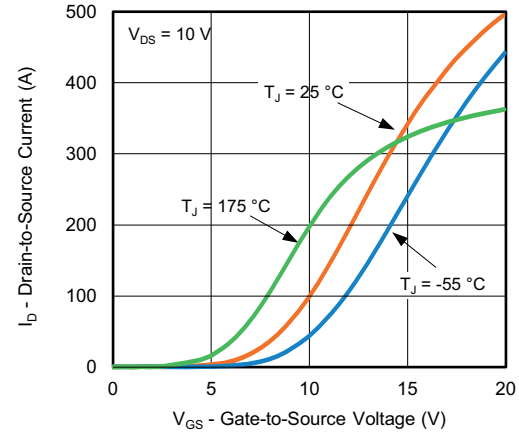
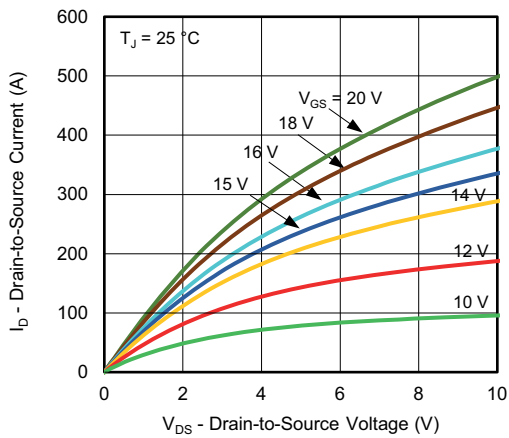
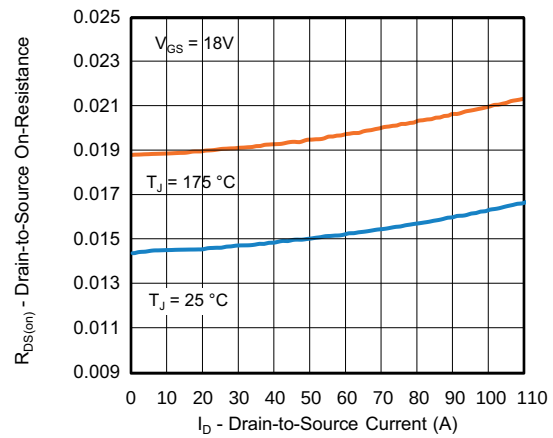
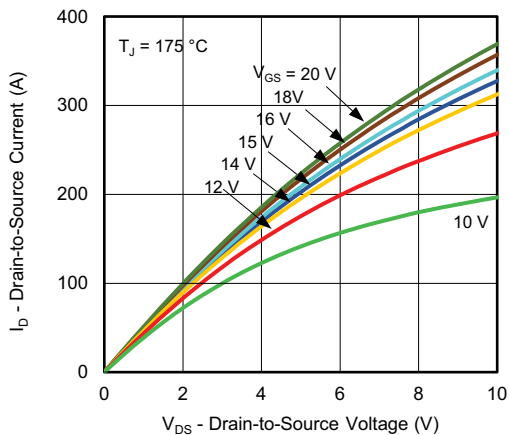
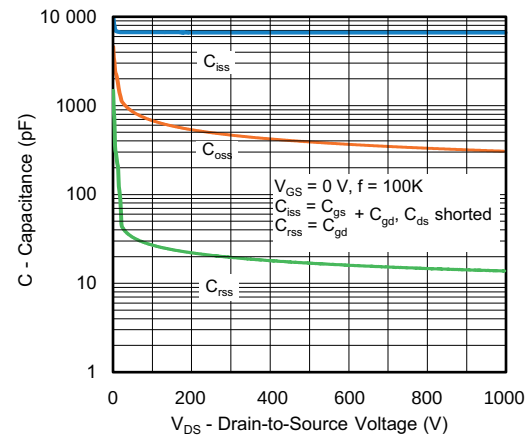
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.28	

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 1 mA		1200	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.70	-	V/°C
Gate-Source Threshold Voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 5 mA		2	-	4	V
Gate-Source Leakage	I _{GSS}	V _{GS} = +18 V		-	-	100	nA
		V _{GS} = - 8 V		-	-	100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 1200V, V _{GS} = 0 V		-	-	100	μA
		V _{DS} = 1200 V, V _{GS} = 0 V, T _J = 125 °C		-	-	200	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 18 V	I _D = 100A	-	0.015	-	Ω
Forward Transconductance	g _{fs}	V _{DS} = 0 V, I _D = 100 A		-	50	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 800 V, f = 100 KHz		-	6800	-	pF
Output Capacitance	C _{oss}			-	300	-	
Reverse Transfer Capacitance	C _{rss}			-	15	-	
Effective Output Capacitance, Energy Related ^a	C _{o(er)}	V _{DS} = 0 V to 800 V, V _{GS} = 0 V		-	230	-	
Effective Output Capacitance, Time Related ^b	C _{o(tr)}			-	320	-	
Total Gate Charge	Q _g	V _{GS} = -5/18 V	I _D = 50 A, V _{DS} = 800 V	-	200	-	nC
Gate-Source Charge	Q _{gs}			-	80	-	
Gate-Drain Charge	Q _{gd}			-	60	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 800 V, I _D =50A V _{GS} = -5/18 V		-	15	20	ns
Rise Time	t _r			-	40	-	
Turn-Off Delay Time	t _{d(off)}			-	60	-	
Fall Time	t _f			-	30	-	
Gate Input Resistance	R _g	f = 1 MHz, open drain		-	8.5	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	60	A
Pulsed Diode Forward Current	I _{SM}			-	-	150	
Diode Forward Voltage	V _{SD}	T _J = 25 °C, I _S = 50 A, V _{GS} = 0		-	-	4.1	V
Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = I _S = 50 A, dI/dt = 1000 A/μs, V _R = 800 V		-	35	-	ns
Reverse Recovery Charge	Q _{rr}			-	1.5	-	μC
Reverse Recovery Current	I _{RRM}			-	15	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 60 % V_{DSS} .
 b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 60 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Typical Transfer Characteristics

Fig. 2 - Typical Output Characteristics

Fig. 5 - Normalized On-Resistance vs. Drain Current

Fig. 3 - Typical Output Characteristics

Fig. 6 - Typical Capacitance vs. Drain-to-Source Voltage

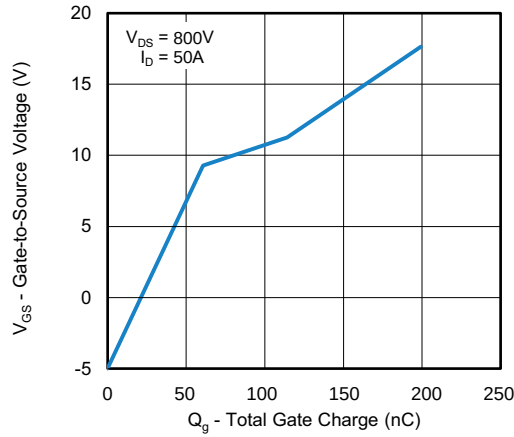


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

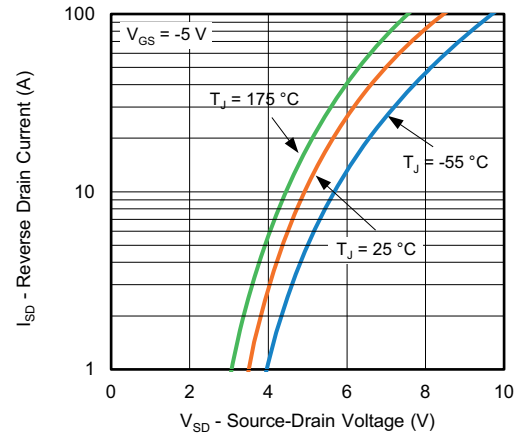


Fig. 10 - Typical Source-Drain Diode Forward Voltage

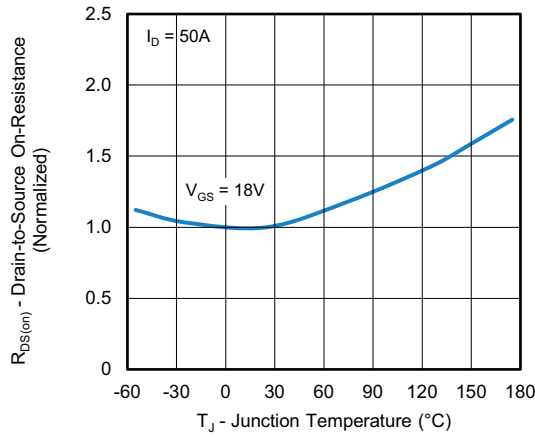


Fig. 8 - Normalized On-Resistance vs. Temperature

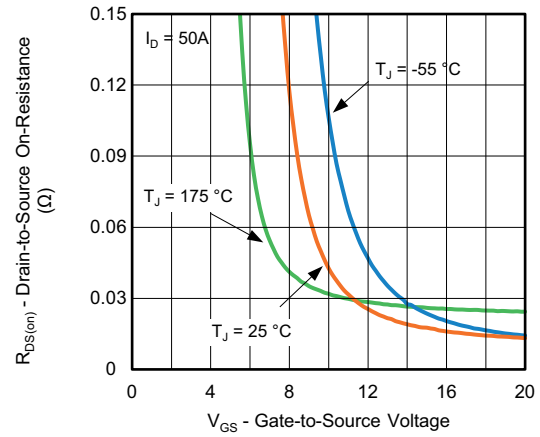


Fig. 11 - On-Resistance vs. Gate-to-Source Voltage

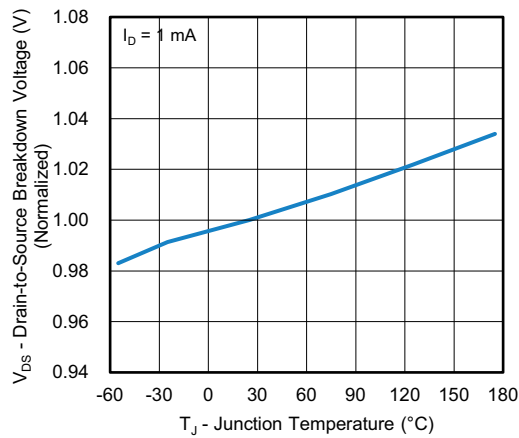


Fig. 9 - Drain-to-Source Voltage vs. Temperature

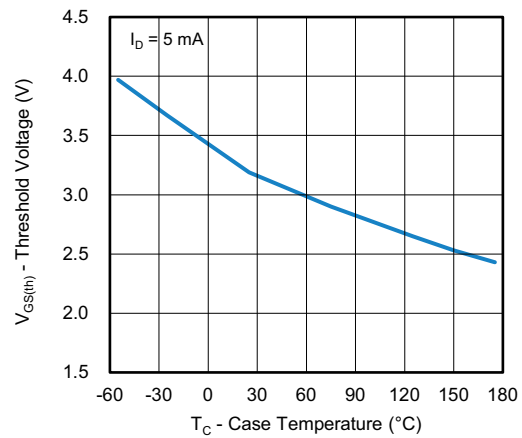


Fig. 12 - Threshold Voltage vs. Case Temperature

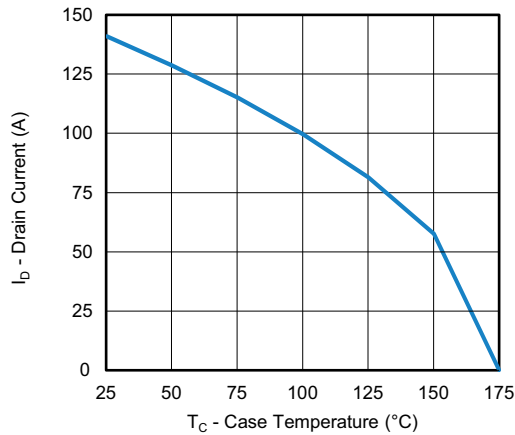


Fig. 13 - Drain Current vs. Case Temperature

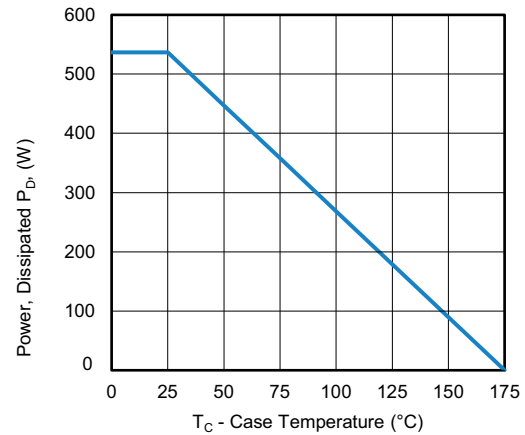


Fig. 15 - Power, Dissipated P_D vs. Case Temperature

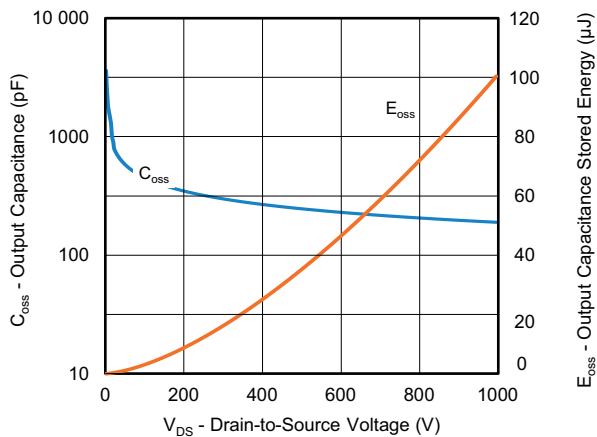


Fig. 14 - Output Capacitance and its Stored Energy vs. Drain-to-Source Voltage

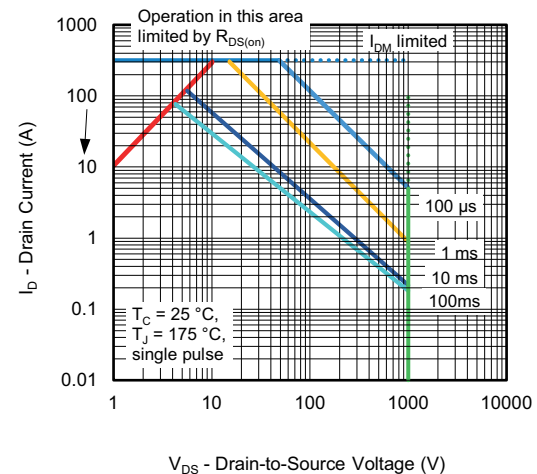


Fig. 16 - Safe Operating Area

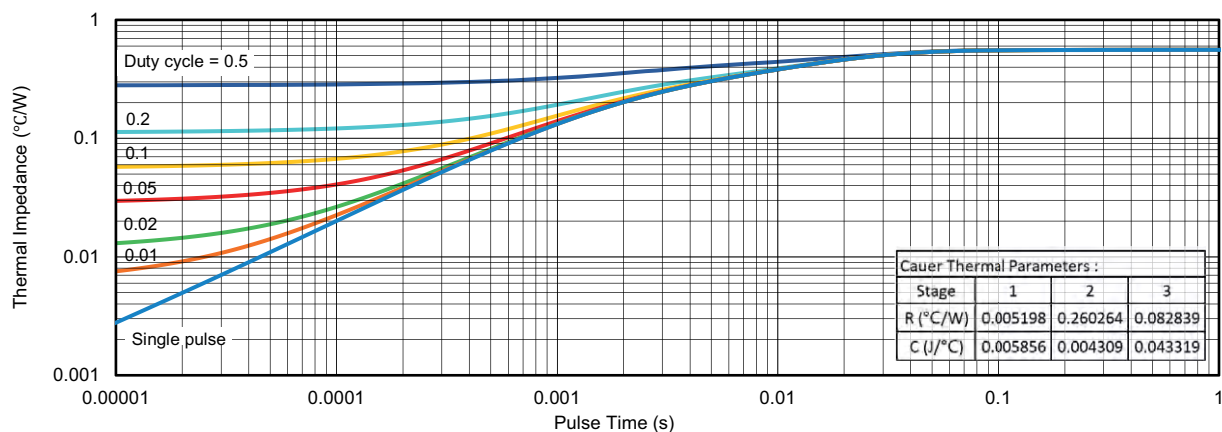


Fig. 17 - Transient Thermal Impedance

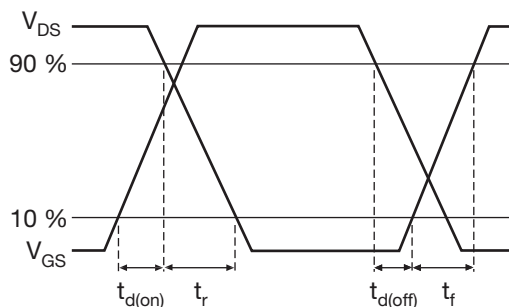


Fig. 18 - Waveforms of Switching Time

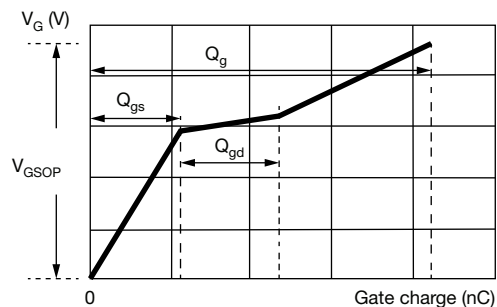


Fig. 21 - Waveforms for Gate Charge

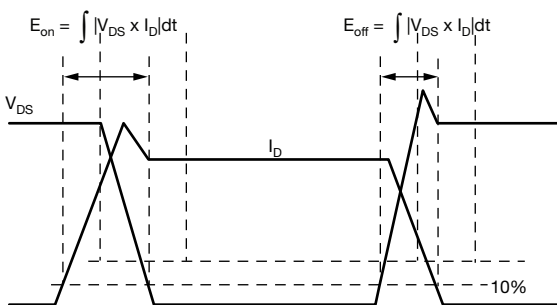


Fig. 19 - Waveforms for Switching Energy

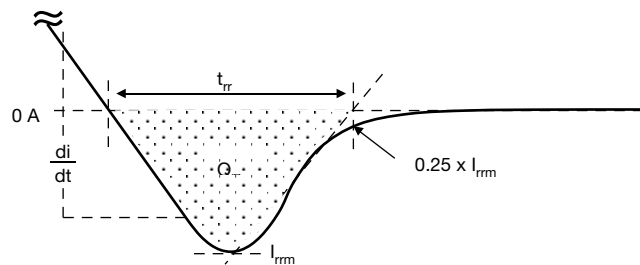


Fig. 22 - Waveforms for Reverse Recovery

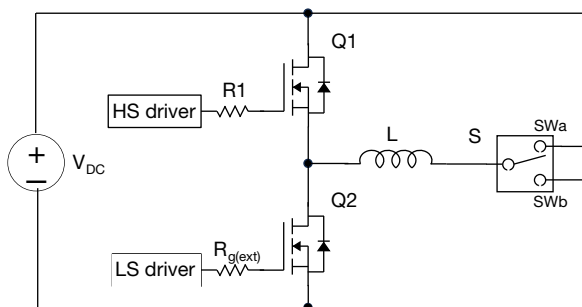


Fig. 20 - Switching and Reverse Diode Characteristics Measurement Circuit

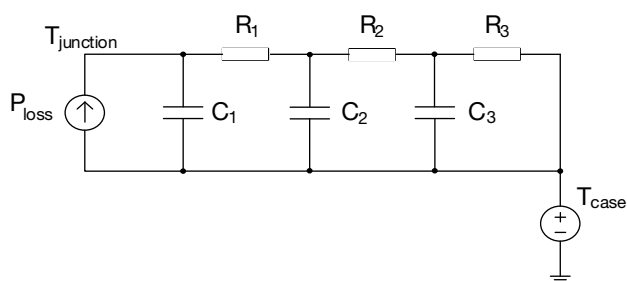
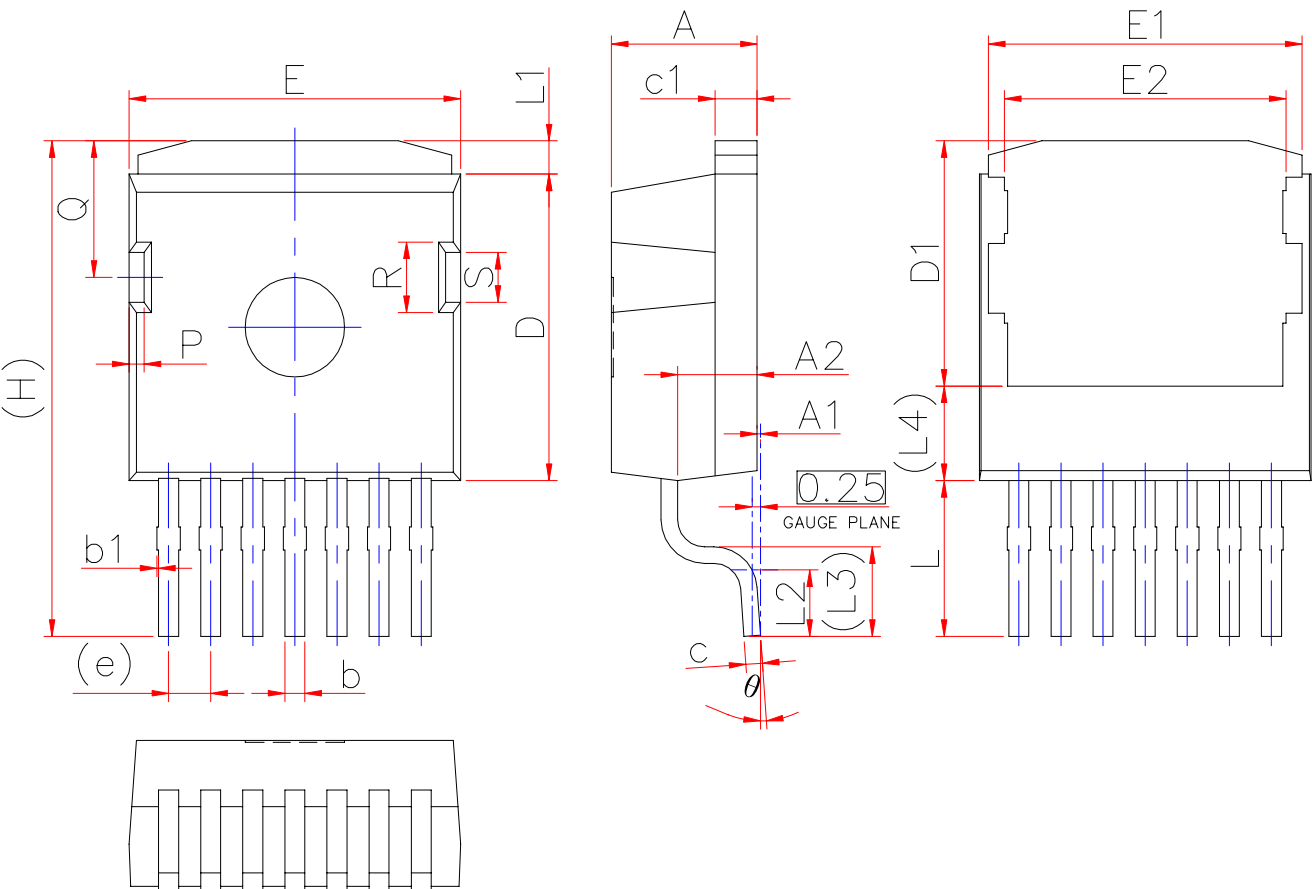


Fig. 23 - Thermal Equivalent Circuit

TO-263-7L(HV) PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters			Dimensions In Inches		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	4.300	4.400	4.500	0.169	0.173	0.177
A1	0.000	0.100	0.200	0.000	0.004	0.008
A2	2.300	2.400	2.500	0.091	0.094	0.098
b	0.500	0.600	0.700	0.020	0.024	0.028
b1	0.000	0.075	0.150	0.000	0.003	0.006
c	0.400	0.500	0.600	0.016	0.020	0.024
c1	1.170	1.270	1.370	0.046	0.050	0.054
D	9.050	9.250	9.450	0.356	0.364	0.372
D1	7.300	7.400	7.500	0.287	0.291	0.295
E	9.800	10.000	10.200	0.386	0.394	0.402
E1	9.360	9.460	9.560	0.369	0.372	0.376
E2	8.400	8.500	8.600	0.331	0.335	0.339
e	1.270 REF.			0.050 REF.		
H	15.000 REF.			0.591 REF.		
L	4.200	4.700	5.200	0.165	0.185	0.205
L1	0.700	1.000	1.300	0.028	0.039	0.051
L2	1.700	2.000	2.300	0.067	0.079	0.091
L3	2.700 REF.			0.106 REF.		
L4	2.850 REF.			0.112 REF.		
P	0.350	0.450	0.550	0.014	0.018	0.022
Q	4.020	4.120	4.220	0.158	0.162	0.166
R	2.030	2.130	2.230	0.080	0.084	0.088
S	1.400	1.500	1.600	0.055	0.059	0.063
θ	0°	4°	8°	0°	4°	8°

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